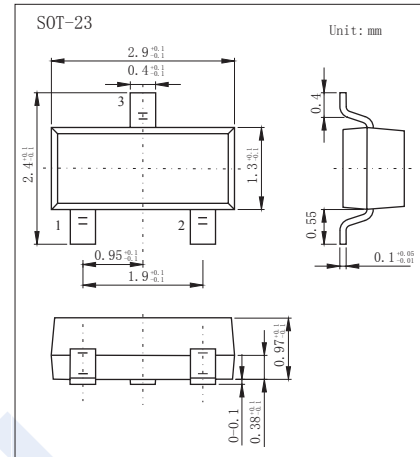
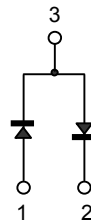


Switching Diodes

DAN217 (KAN217)

■ Features

- Ultra high speed switching
- High reliability

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--|--------------------|------------|------------------|
| Reverse Voltage | V_{RM} | 80 | V |
| Reverse Voltage (DC) | V_R | 80 | |
| Average rectified forward current (Single) | I_o | 100 | mA |
| Forward Current (Single) | I_{FM} | 300 | |
| Surge current ($t=1\mu\text{s}$) | I_{surge} | 4 | A |
| Power Dissipation | P_d | 200 | mW |
| Junction Temperature | T_J | 150 | $^\circ\text{C}$ |
| Storage Temperature range | T_{stg} | -55 to 150 | |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---------------------------------|----------|--|-----|-----|-----|---------------|
| Reverse breakdown voltage | V_R | $I_R = 100 \mu\text{A}$ | 80 | | | V |
| Forward voltage | V_F | $I_F = 100 \text{ mA}$ | | | 1.2 | |
| Reverse voltage leakage current | I_R | $V_R = 70 \text{ V}$ | | | 0.1 | μA |
| Capacitance between terminals | C_t | $V_R = 6 \text{ V}, f = 1 \text{ MHz}$ | | | 3.5 | pF |
| Reverse recovery time | t_{rr} | $V_R = 6 \text{ V}, I_F = 5 \text{ mA}, R_L = 50 \Omega$ | | | 4 | ns |

■ Marking

| | |
|---------|-----|
| Marking | BA* |
|---------|-----|

Switching Diodes

DAN217 (KAN217)

Typical Characteristics

